
HAT1024R

Silicon P Channel Power MOS FET
High Speed Power Switching

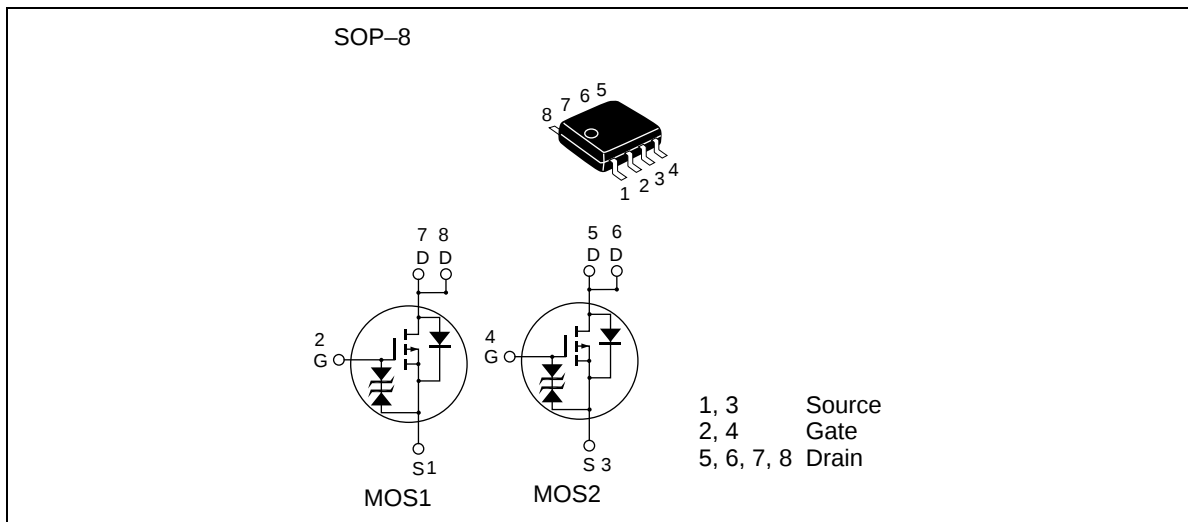
HITACHI

ADE-208-476 F (Z)
7th. Edition
October. 1996

Features

- Low on-resistance
- Capable of 4 V gate drive
- Low drive current
- High density mounting

Outline



HAT1024R

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DS}	−30	V
Gate to source voltage	V_{GS}	±20	V
Drain current	I_D	−3.5	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	−28	A
Body–drain diode reverse drain current	I_{DR}	−3.5	A
Channel dissipation	P_{ch} ^{Note2}	2	W
Channel dissipation	P_{ch} ^{Note3}	3	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

Note: 1. $PW \leq 10\mu s$, duty cycle $\leq 1\%$

2. 1 Drive operation : When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), $PW \leq 10s$

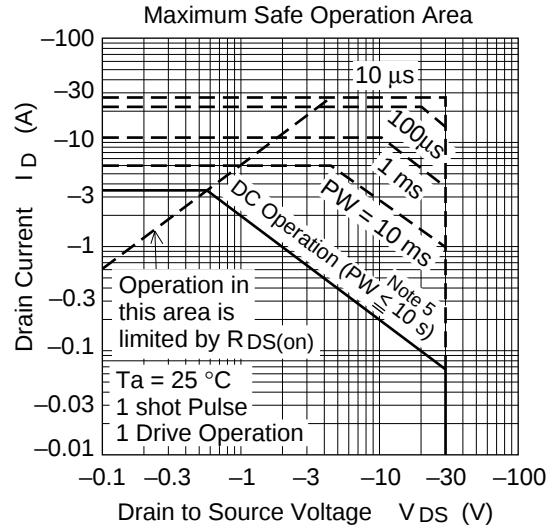
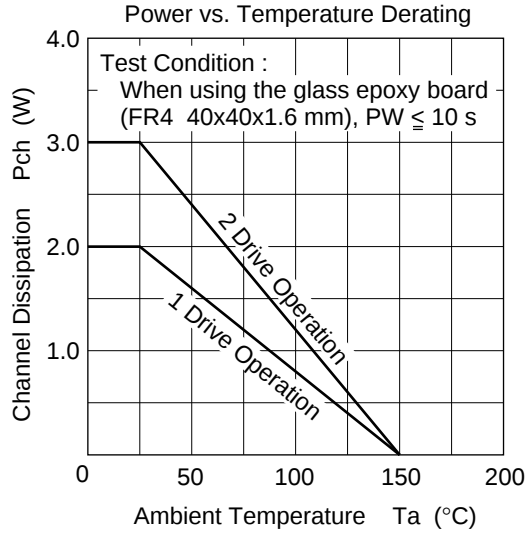
3. 2 Drive operation : When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), $PW \leq 10s$

Electrical Characteristics (Ta = 25°C)

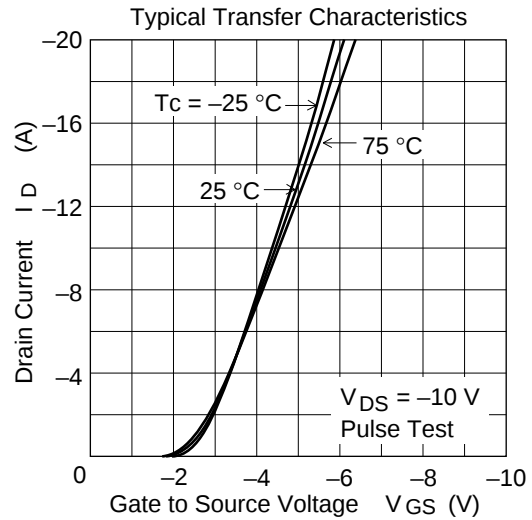
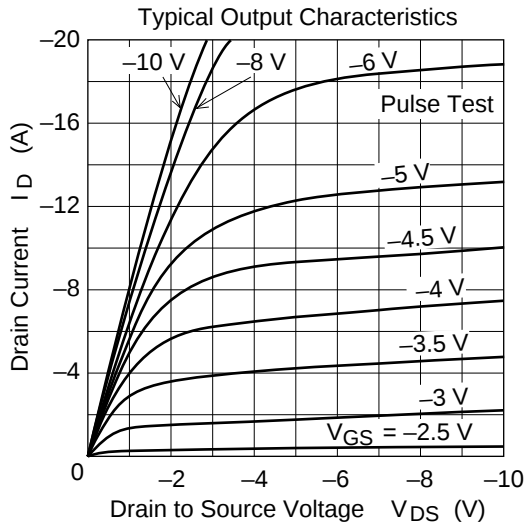
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-30	—	—	V	$I_D = -10mA, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = \pm 100\mu A, V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 16V, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-10	μA	$V_{DS} = -30V, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.5	V	$V_{DS} = -10V, I_D = -1mA$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.12	0.16	Ω	$I_D = -2A, V_{GS} = -10V$ ^{Note4}
	$R_{DS(on)}$	—	0.2	0.34	Ω	$I_D = -2A, V_{GS} = -4V$ ^{Note4}
Forward transfer admittance	$ y_{fs} $	2.5	3.5	—	S	$I_D = -2A, V_{DS} = -10V$ ^{Note4}
Input capacitance	C_{iss}	—	350	—	pF	$V_{DS} = -10V$
Output capacitance	C_{oss}	—	230	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	75	—	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}$	—	18	—	ns	$V_{GS} = -4V, I_D = -2A$
Rise time	t_r	—	110	—	ns	$V_{DD} \cong -10V$
Turn-off delay time	$t_{d(off)}$	—	20	—	ns	
Fall time	t_f	—	30	—	ns	
Body-drain diode forward voltage	V_{DF}	—	-1.0	-1.5	V	$I_F = -3.5A, V_{GS} = 0$ ^{Note4}
Body-drain diode reverse recovery time	t_{rr}	—	60	—	ns	$I_F = -3.5A, V_{GS} = 0$ $diF/dt = 20A/\mu s$

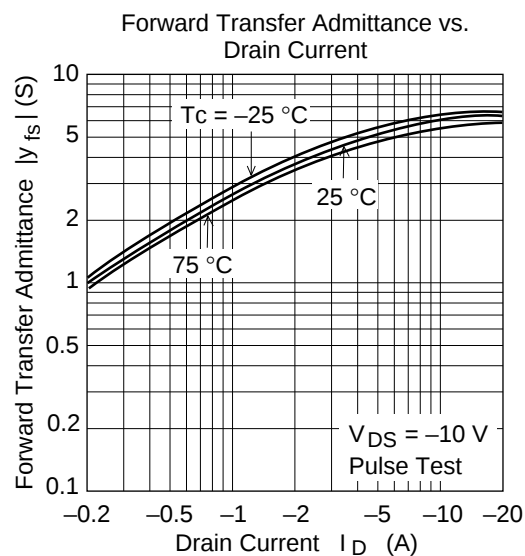
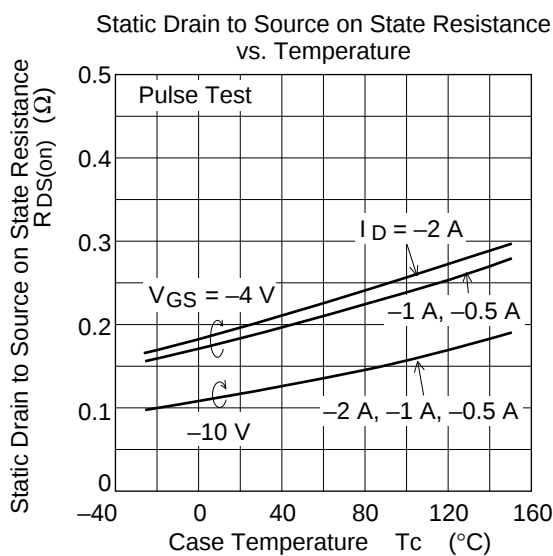
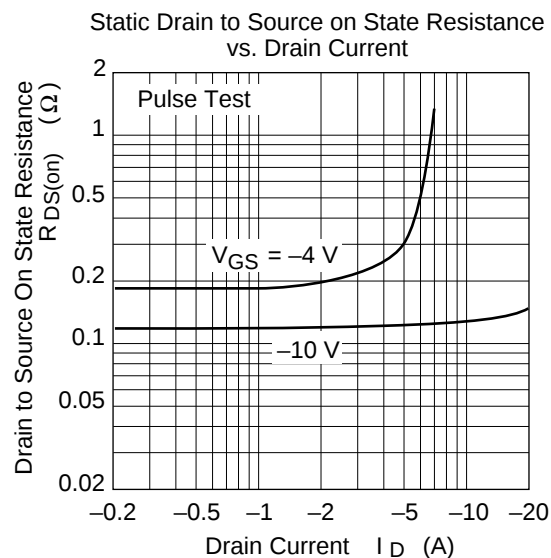
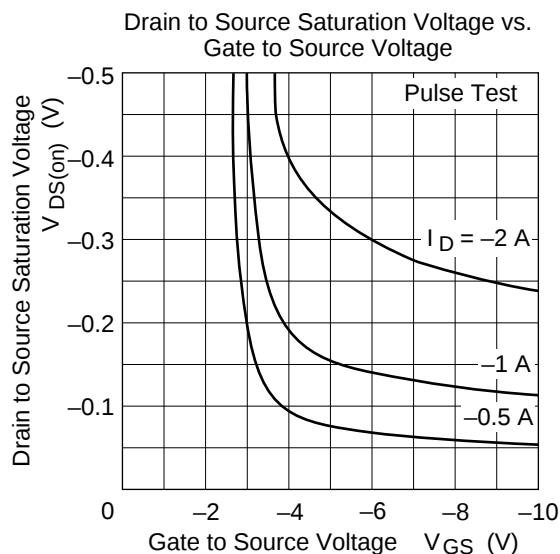
Note: 4. Pulse test

Main Characteristics

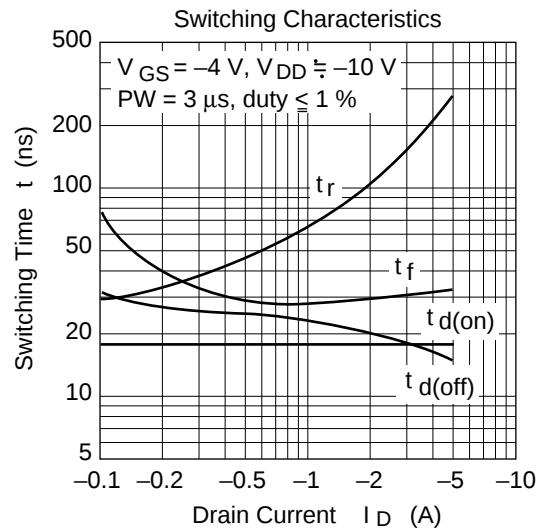
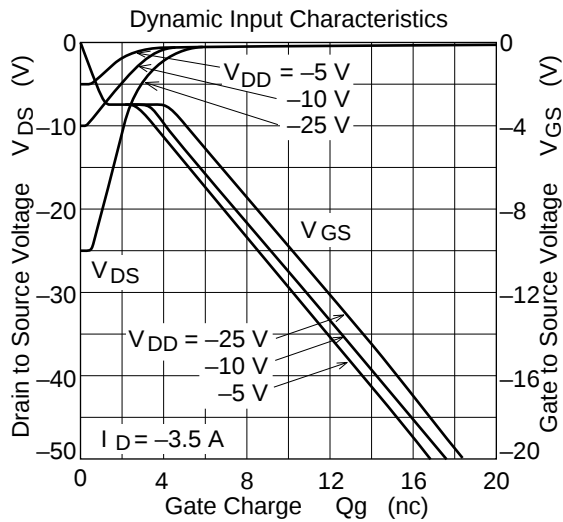
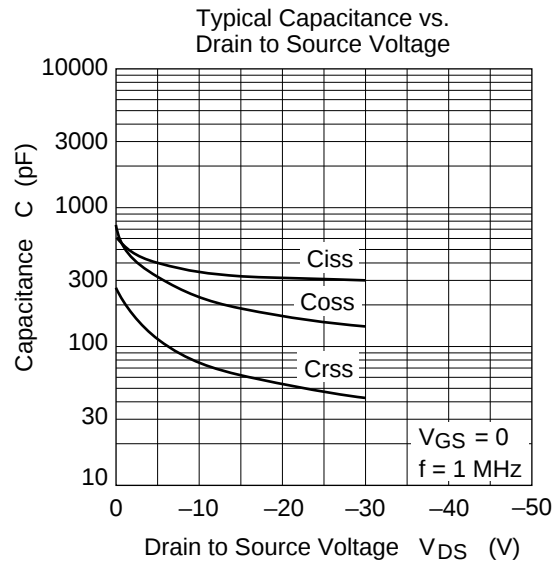
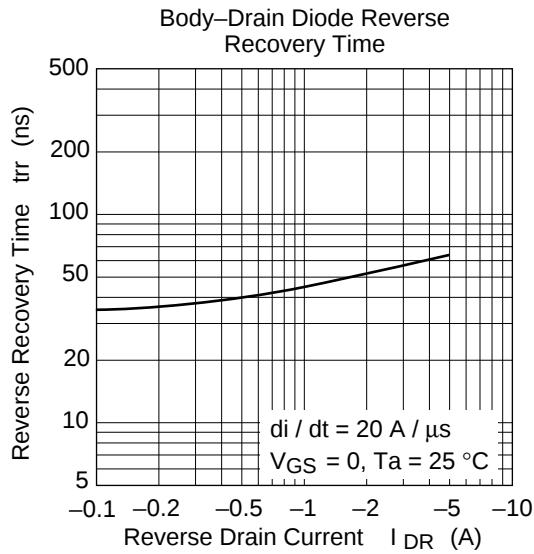


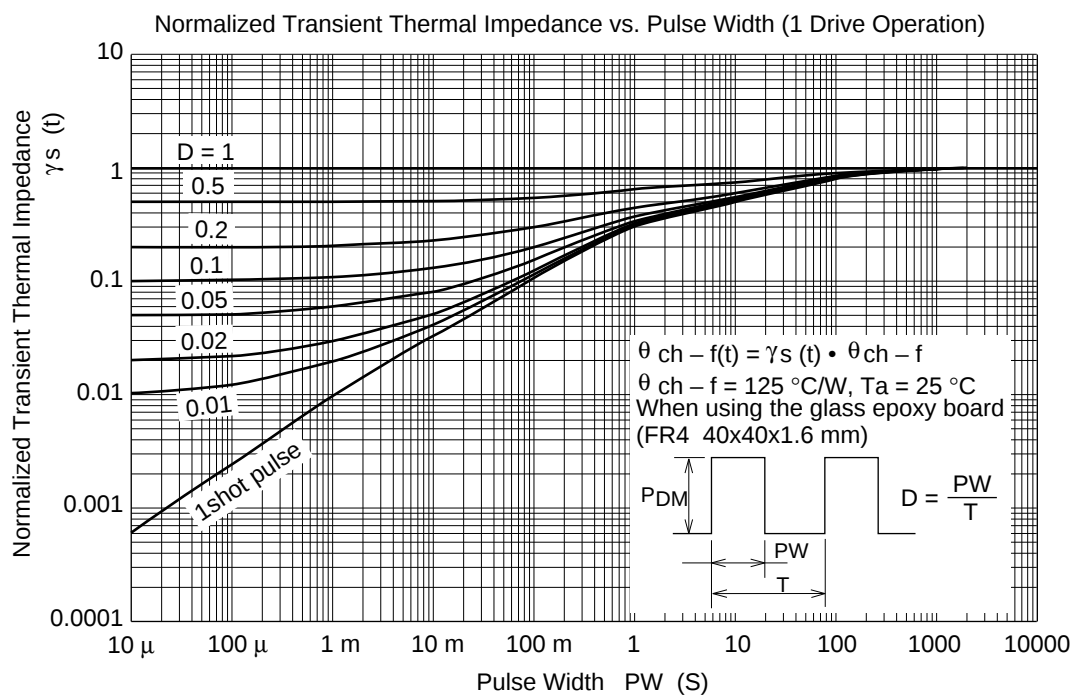
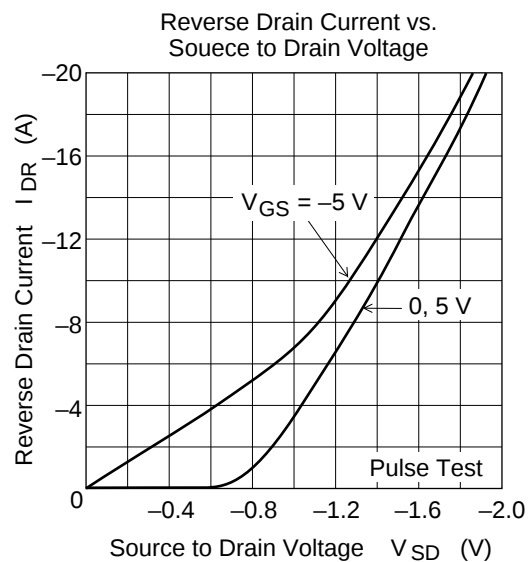
Note 5 :
When using the glass epoxy board
(FR4 40x40x1.6 mm)

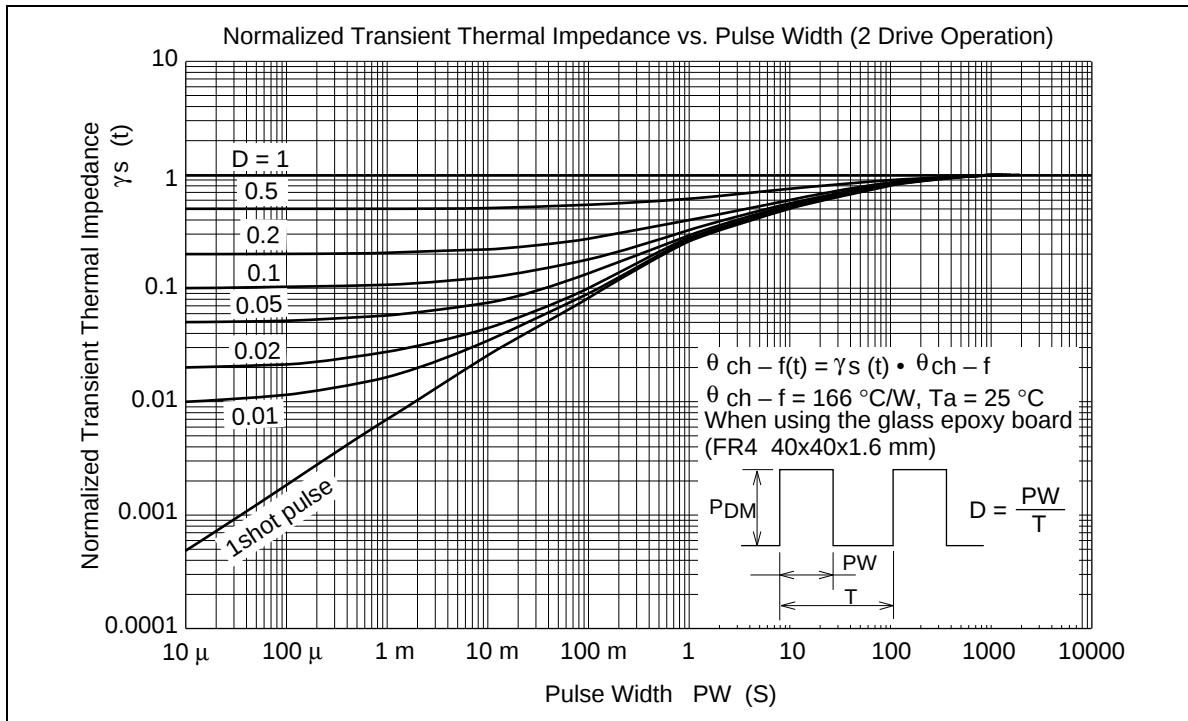




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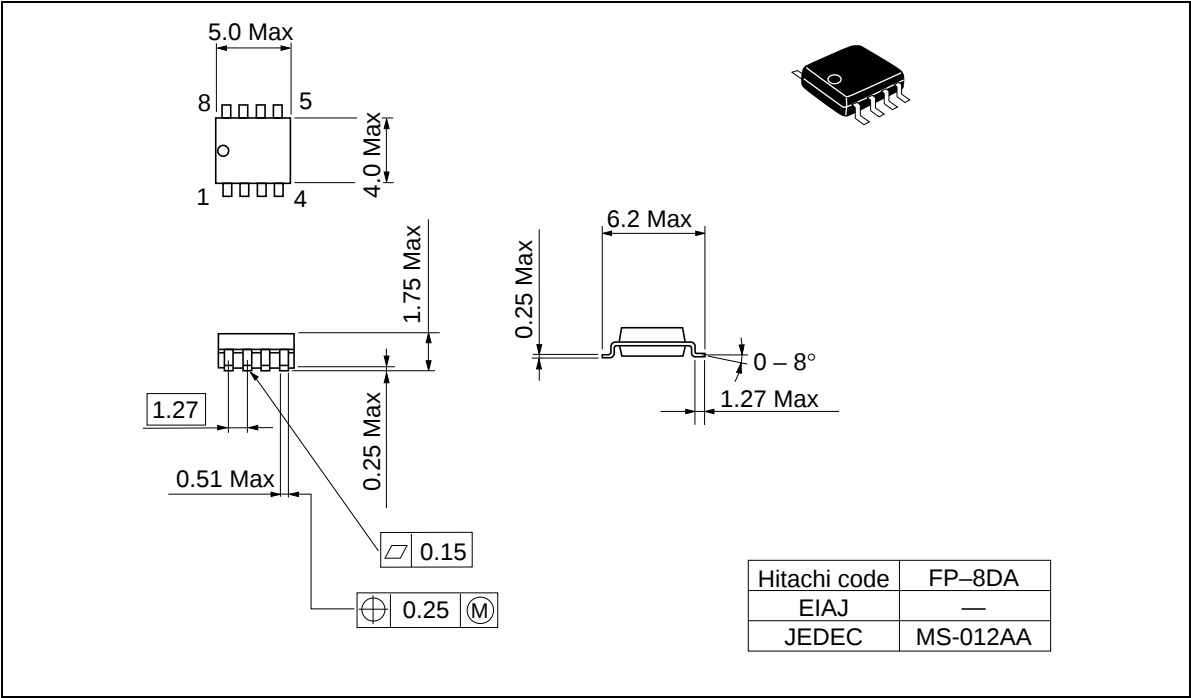






Package Dimentions

Unit: mm



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